Unitized Semiconductor Devices - Page 1 of 2



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Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.225 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Component Name And Quantity:

2 transistor

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open all transistor and 80.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter all transistor and 8.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

10.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

50.0 watts small-signal input power, common-collector preset all transistor

Transfer Ratio:

800.0 static forward current transfer ratio, common-emitter all transistor

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: npn

Precious Material And Location:

Lead surfaces gold

Precious Material:

Gold

Terminal Type And Quantity:

8 pin

Shelf Life:

N/a

Unit Of Measure:



Demilitarization:

No

Fiig:

A110a0